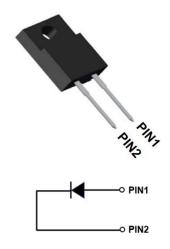






Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _{F(135°C)}	2.5A
Q _C	10.2nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

Package: ITO-220AC
 Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_C=25 °C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D112002FYG4
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	V	1200
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200
Continuous forward current @ T _C =25°C			5.3
Continuous forward current @ T _c =135°C	l _F	Α	2.5
Continuous forward current @ T _C =147°C			2
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	20
Power Dissipation@ T _C =25°C	В	W	23.8
Power Dissipation@ T _C =110°C	P _{TOT}	VV	10.3
i²t Value@ Tc=25°C ,tp=10ms	∫ i²dt	A ² S	2
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175





■Electrical Characteristics

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V _F	V	I _F =2A, T _j =25°C	1.45	1.60
			I _F =2A, T _j =175°C	2.17	-
Reverse current	I _R	μA	V _R =1200V, T _j =25°C	0.1	20
			V _R =1200V, T _j =175°C	0.5	-
Total capacitive charge	Q _C	nC	V_R =800V, T_j =25°C, Q_C = $\int_0^{VR} C(V) dV$	10.2	-
Total capacitance	O	pF	V _R =0V, f=1MHZ	127	-
			V _R =400V, f=1MHZ	9.8	-
			V _R =800V, f=1MHZ	7.5	-
Capacitance stored energy	Ec	μJ	V _R =800V	2.6	-

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	R _{eJ-C}	°C W	6.30

■Typical Characteristics

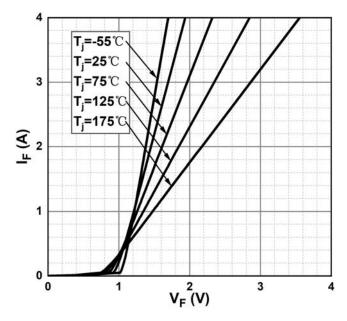


Figure 1. Forward Characteristics

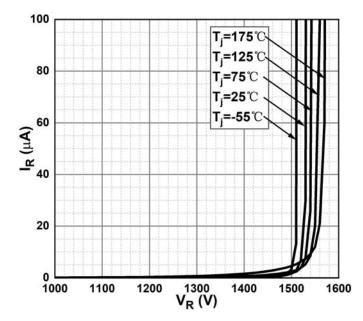
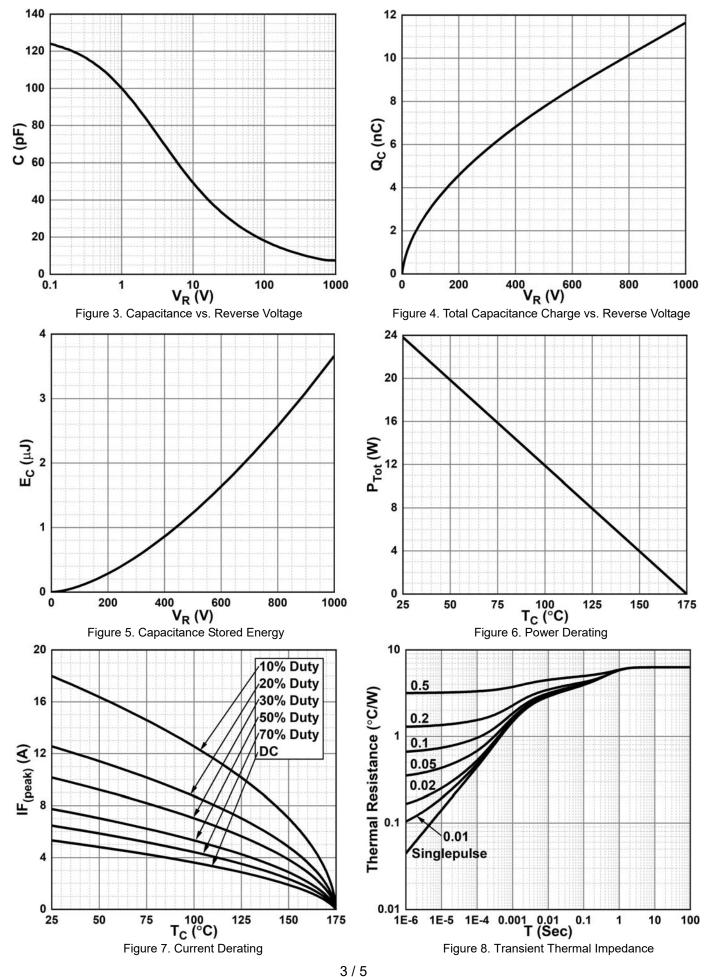


Figure 2. Reverse Characteristics



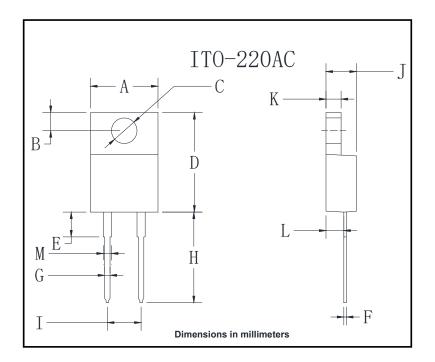








■Outline Dimensions



ITO-220AC				
Dim	Min	Max		
Α	9.8	10.2		
В	2.25	2.75		
С	2.95	3.45		
D	14.75	15.25		
E	3.5	4.1		
F	0.45	0.75		
G	0.45	0.75		
Н	13.35	14.15		
I	4.97	5.23		
J	4.3	4.8		
K	2.5	2.74		
L	2.58	2.82		
М	1.03	1.43		



YJD112002FYG4



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